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(71) Applicant: **INTERNATIONAL BUSINESS MACHINES CORPORATION** [US/US]; New Orchard Road, Armonk, New York 10504 (US).

(71) Applicant (for MG only): **IBM (CHINA) CO., LIMITED** [CN/CN]; 7F, Bldg 10, Zhangjiang Innovation Park,

399 Keyuan Road, Zhangjiang High-Tech Campus, Pudong New Area, Shanghai 201203 (CN).

(72) Inventors: **CHIDAMBARRAO, Dureseti**; 2070 Route 52, Hopewell Junction, New York 12533-6683 (US). **WOLPERT, David**; 2455 South Rd, Poughkeepsie, New York 12601-5400 (US). **OGINO, Atsushi**; 2070 Route 52, Hopewell Junction, New York 12533 (US). **GUZOWSKI, Matthew T.**; 326 IBM Road, Williston, Vermont 05495-7907 (US). **OSTRANDER, Steven Paul**; 2070 Route 52, Hopewell Junction, New York 12533-6683 (US). **SINHA, Tuhin**; 2455 South Rd, Poughkeepsie, New York 12601-5400 (US). **GRAY, Michael Stewart**; 2455 South Rd, Poughkeepsie, New York 12601-5400 (US).

(74) Agent: **CCPIT PATENT AND TRADEMARK LAW OFFICE**; 10/F, Ocean Plaza, 158 Fuxingmennei Street, Beijing 100031 (CN).

(54) Title: STACKED VIA RIVETS IN CHIP HOTSPOTS

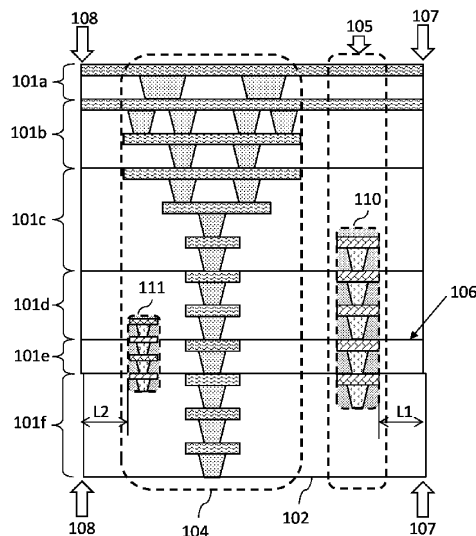


Fig. 1A

(57) Abstract: A structure including a plurality of dielectric regions is described. The structure can include a rivet cell. The rivet cell can include a set of stacked vias. The rivet cell can extend through a stress hotspot of the structure. A length of the rivet cell can thread through at least one dielectric region among the plurality of dielectric regions. The rivet cell can be among a number of rivet cells inserted in the stress hotspot. The stress hotspot can be among a plurality of stress hotspots across the structure. A length of the rivet cell can be based on a model of a relationship between the length of the rivet cell and an energy release rate of the structure. The rivet cell can thread through an interface between a first dielectric region and a second dielectric region having different dielectric constants.

[Continued on next page]

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